

Ref #	Hits	Search Query	DBs	Default Operator	Plural S	Time Stamp
L1	0	10/695249	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 12:56
L2	12920	((opening trench hole via groove damascene recess) with substrate) with (diffusion diffus\$4)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:17
L3	2815	2 and ((opening trench hole via groove damascene recess) with substrate) with (barrier line lining seed)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:37
L4	1759	3 and ((opening trench hole via groove damascene recess) with substrate) with (conduct\$3 metal\$5)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:01
L5	525	4 and ((heat\$4 anneal\$4 thermal\$5) with (ion dopant activ\$4 dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:10
L6	83	5 and ( electroless plating electroplating)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:09
L7	596	4 and ((heat\$4 anneal\$4 thermal\$5) with (impurity ion dopant activ\$4 dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:15
L8	407	7 and (planar planized planarization polish\$3 'cmp' chemical adj mechanical)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:16
L9	192	8 and ((opening trench hole via groove damascene recess) with (isulat\$4 dielectric))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:22
L10	52	9 and boundary	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:23

L11	78	9 and interface	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:24
L12	41	9 and grain	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:23
L13	2241	2 and ((opening trench hole via groove damascene recess) with substrate) with (metal)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:38
L14	139	13 and ((opening trench hole via groove damascene recess) with substrate) with (refractory noble)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:40
L15	4800	2 and ((opening trench hole via groove damascene recess) with substrate) with (metal conduct\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:38
L16	139	14 and ((opening trench hole via groove damascene recess) with substrate) with (refractory noble)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:43
L17	201	13 and ((opening trench hole via groove damascene recess) with (refractory noble))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:40
L18	141	15 and ((opening trench hole via groove damascene recess) with substrate) with (refractory noble)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:43

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L1	0	10/695249	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 12:56
L2	12920	((opening trench hole via groove damascene recess) with substrate) with (diffusion diffus\$4)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:45
L3	2815	2 and ((opening trench hole via groove damascene recess) with substrate) with (barrier line lining seed)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:37
L4	1759	3 and ((opening trench hole via groove damascene recess) with substrate) with (conduct\$3 metal\$5)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:44
L5	525	4 and ((heat\$4 anneal\$4 thermal\$5) with (ion dopant activ\$4 dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:10
L6	83	5 and ( electroless plating electroplating)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:09
L7	596	4 and ((heat\$4 anneal\$4 thermal\$5) with (impurity ion dopant activ\$4 dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:15
L8	407	7 and (planar planized planarization polish\$3 'cmp' chemical adj mechanical)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:51
L9	192	8 and ((opening trench hole via groove damascene recess) with (isulat\$4 dielectric))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:22
L10	52	9 and boundary	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 16:10

L11	78	9 and interface	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:24
L12	41	9 and grain	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 13:23
L13	2241	2 and ((opening trench hole via groove damascene recess) with substrate) with (metal)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:38
L14	139	13 and ((opening trench hole via groove damascene recess) with substrate) with (refractory noble)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:40
L15	4800	2 and ((opening trench hole via groove damascene recess) with substrate) with (metal conduct\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:38
L16	139	14 and ((opening trench hole via groove damascene recess) with substrate) with (refractory noble)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:43
L17	201	13 and ((opening trench hole via groove damascene recess) with (refractory noble))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:40
L18	141	15 and ((opening trench hole via groove damascene recess) with substrate) with (refractory noble)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:43
L19	12920	((opening trench hole via groove damascene recess) with substrate) with (diffusion diffus\$4)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:45
L20	6640	19 and ((opening trench hole via groove damascene recess) with (metal metall\$5 conducti\$3))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:47
L21	4169	20 and ((opening trench hole via groove damascene recess) with (ion impurity dopant dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:49

L22	2011	21 and ((heat\$3 anneal\$3 thermal) with (ion impurity dopant dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:48
L23	437	22 and ((migrat\$3 interfac\$3 boundary) with (ion impurity dopant dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 16:00
L24	263	23 and (planar planized planarization polish\$3 'cmp' chemical adj mechanical)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:52
L25	97	24 and interconnect\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 15:52
L26	382	22 and ((interfac\$3 boundary) with (ion impurity dopant dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 16:00
L27	258	22 and (interfac\$3 with (ion impurity dopant dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 16:01
L28	46	27 and (boundary with (ion impurity dopant dop\$2))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/11 16:01